

DMT2005UDV

DUAL 24V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (Type UXC)

Product Summary

BV _{DSS}	R _{DS(ON) max}	I _D T _A = +25°C
24V	7mΩ @ V _{GS} = 10V	50
	$8m\Omega @ V_{GS} = 4.5V$	47
	10mΩ @ V _{GS} = 3.7V	42
	$12m\Omega$ @ $V_{GS} = 2.5V$	38

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Power Management Functions
- Analog Switch

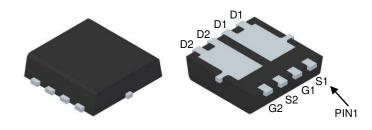
Features

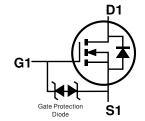
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

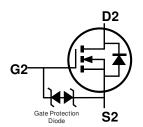
Mechanical Data

- Case: PowerDI[®]3333-8 (Type UXC)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.072 grams (Approximate)

PowerDI3333-8 (Type UXC)







Top View **Bottom View**

Equivalent Circuit

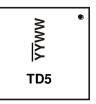
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT2005UDV-7	PowerDI3333-8 (Type UXC)	2,000/Tape & Reel
DMT2005UDV-13	PowerDI3333-8 (Type UXC)	3000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



TD5 = Product Type Marking Code YYWW = Date Code Marking \overline{YY} = Last Two Digits of Year (ex: 18 for 2018) WW = Week Code (01 to 53)

Document number: DS39727 Rev. 2 - 2



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	24	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 7) V _{GS} = 10V	Steady State	$T_C = +25$ °C $T_C = +70$ °C	I _D	50 40	А
Maximum Body Diode Forward Current (Note 7)			Is	30	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	70	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	70	Α
Avalanche Current (Note 8) L = 0.1mH			I _{AS}	26	Α
Avalanche Energy (Note 8) L = 0.1mH			Eas	34	mJ

Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P_{D}	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	141	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P_{D}	1.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	66	°C/W
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	4.8	°C/W
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

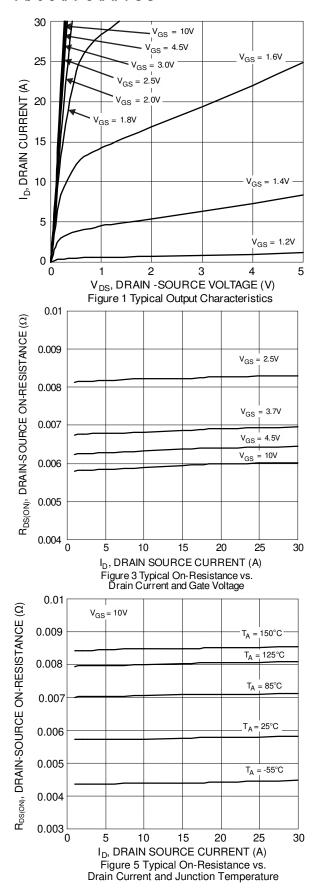
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

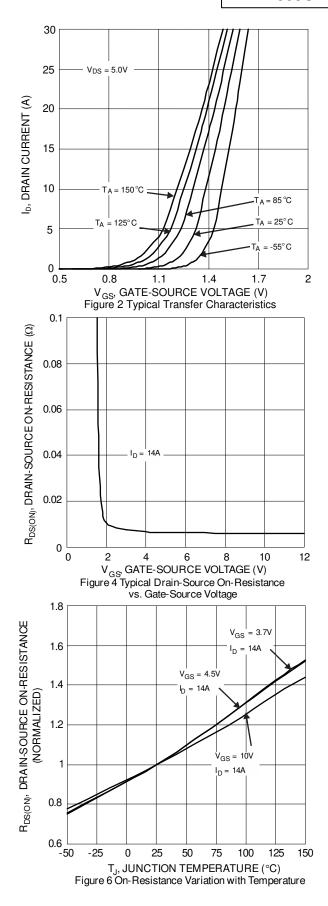
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	24	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current (T _J = +25°C)	I _{DSS}	_	_	1	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 10V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	0.5	_	1.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
		_	5.9	7.0		$V_{GS} = 10V, I_D = 14A$	
Static Drain-Source On-Resistance	D	_	6.3	8.0	mΩ	$V_{GS} = 4.5V, I_D = 14A$	
Static Drain-Source On-Nesistance	R _{DS(ON)}	_	6.7	10.0	11152	$V_{GS} = 3.7V, I_D = 14A$	
		_	8.9	12.0		$V_{GS} = 2.5V, I_D = 13A$	
Diode Forward Voltage	V_{SD}	_	0.7	1.2	V	$V_{GS} = 0V$, $I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	2,060	_		V 40V V 0V	
Output Capacitance	Coss	_	547	-	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	517	1		I = 1.0WII IZ	
Gate Resistance	R_{G}	_	1.6	1	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_g	_	24.8	_			
Total Gate Charge (V _{GS} = 10V)	Q_g	_	46.7	1	nC	$V_{DD} = 10V, I_D = 5A$	
Gate-Source Charge	Q _{gs}	_	3	_	IIC		
Gate-Drain Charge	Q_{gd}	_	9.6	_			
Turn-On Delay Time	t _{D(ON)}	_	3.7	_		$V_{DD} = 10V$, $V_{GS} = 10V$, $R_G = 3\Omega$, $I_D = 5A$	
Turn-On Rise Time	t _R	_	7.2	_			
Turn-Off Delay Time	t _{D(OFF)}	_	37.5	_	ns		
Turn-Off Fall Time	t _F	_	23.3	_			
Reverse Recovery Time	t _{RR}	_	19.9	_	ns	L 50 di/d+ 1000/	
Reverse Recovery Charge	Q _{RR}	_	9.0	_	nC	I _F = 5A, di/dt = 100A/μs	

- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_{J} = +25^{\circ}C$.
- 9. Short duration pulse test used to minimize self-heating effect.

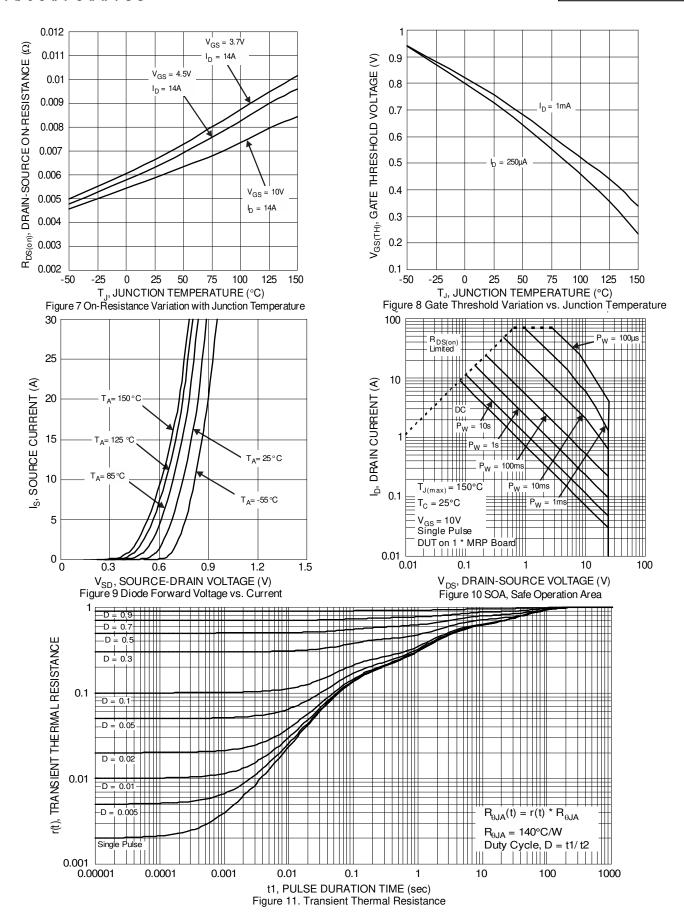
 10. Guaranteed by design. Not subject to product testing.



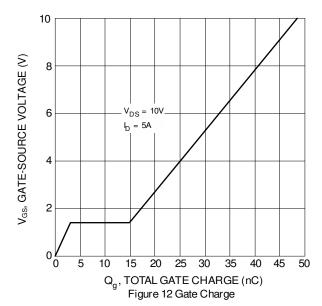










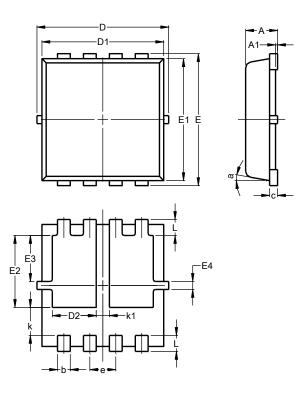




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UXC)

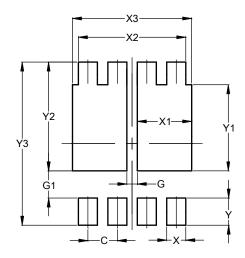


PowerDI3333-8						
(Type UXC)						
Dim	Min	Тур				
Α	0.75	0.85	0.80			
A 1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	0.90	1.30	1.10			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	-	-	0.65			
L	0.30	0.50	0.40			
k	0.50	0.90	0.70			
k1	0.13	0.53	0.33			
а	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UXC)



Dimensions	Value (in mm)
C	0.650
G	0.230
G1	0.600
Х	0.420
X1	1.200
X2	2.370
Х3	2.630
Υ	0.600
Y1	1.900
Y2	2.400
Y3	3.600



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